

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

TK32E12N1

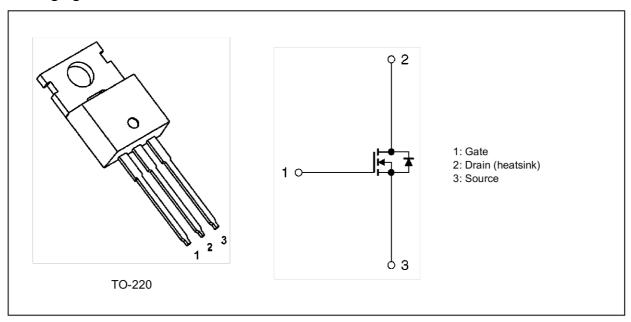
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 11.0 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (2) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max)} \text{ (V}_{DS} = 120 \text{ V)}$
- (3) Enhancement mode: $V_{th} = 2.0 \text{ to } 4.0 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	120	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25°C)	(Note 1)	I _D	60	Α
Drain current (DC)		(Note 1), (Note 2)	I _D	32	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	110	
Power dissipation	(T _c = 25°C)		P_D	98	W
Single-pulse avalanche energy		(Note 3)	E _{AS}	48	mJ
Avalanche current			I _{AR}	32	Α
Channel temperature			T _{ch}	150	℃
Storage temperature			T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.27	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted with heatsink so that $R_{\text{th(ch-a)}}$ becomes 4.16°C/W.

Note 3: V_{DD} = 80 V, T_{ch} = 25°C (initial), L = 46.1 μ H, I_{AR} = 32 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Rev.4.0



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V	1	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	120	_	_	V
Drain-source breakdown voltage (Note 4)	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	90	_	_	
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ mA}$	2.0	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 16 A		11.0	13.8	mΩ

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 60 V, V _{GS} = 0 V, f = 1 MHz	_	2000	_	pF
Reverse transfer capacitance	C _{rss}		_	13		
Output capacitance	C _{oss}		_	330		
Gate resistance	r _g	_	_	1.9	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	14	_	ns
Switching time (turn-on time)	t _{on}		_	33	_	
Switching time (fall time)	t _f		_	14	_	
Switching time (turn-off time)	t _{off}		_	43		

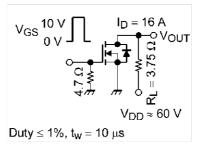


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 96 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}$		34		nC
Gate-source charge 1	Q _{gs1}			13		
Gate-drain charge	Q_{gd}		_	9.8	_	
Gate switch charge	Q _{SW}		_	15	_	



6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 5)	I _{DR}	_	_	_	32	Α
Reverse drain current (pulsed)	(Note 5)	I _{DRP}	_	_	_	110	
Diode forward voltage		V _{DSF}	I _{DR} = 32 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	(Note 6)	t _{rr}	I _{DR} = 32 A, V _{GS} = 0 V	_	73	_	ns
Reverse recovery charge	(Note 6)	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	160	_	nC

Note 5: Ensure that the channel temperature does not exceed 150°C.

Note 6: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking

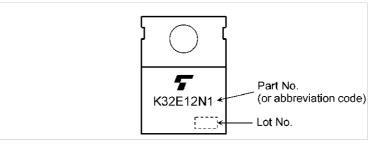
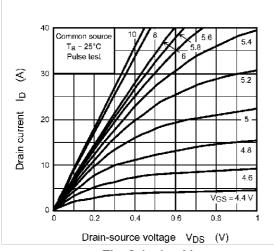


Fig. 7.1 Marking



8. Characteristics Curves (Note)



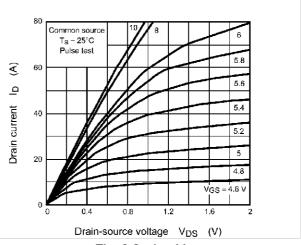
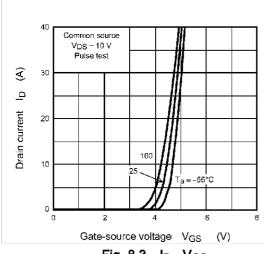


Fig. 8.1 ID - VDS

Fig. 8.2 I_D - V_{DS}



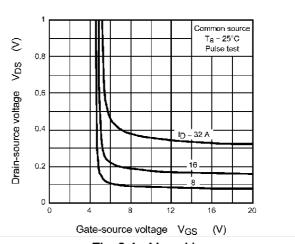
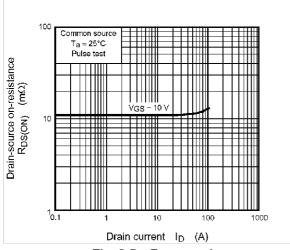


Fig. 8.3 I_D - V_{GS}

Fig. 8.4 V_{DS} - V_{GS}



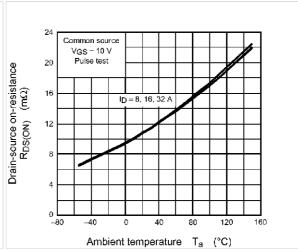
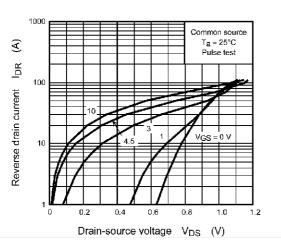


Fig. 8.5 R_{DS(ON)} - I_D

Fig. 8.6 R_{DS(ON)} - T_a

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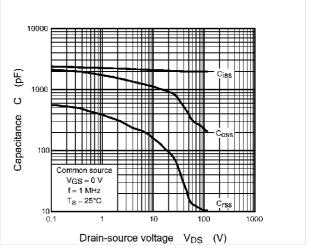


Fig. 8.8 Capacitance - V_{DS}

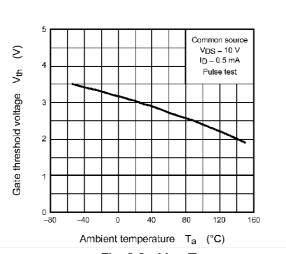


Fig. 8.9 V_{th} - T_a

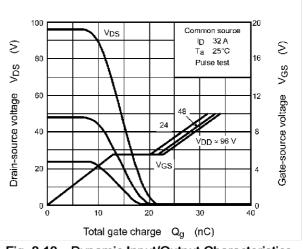


Fig. 8.10 Dynamic Input/Output Characteristics

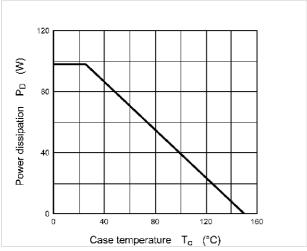


Fig. 8.11 P_D - T_c (Guaranteed Maximum)



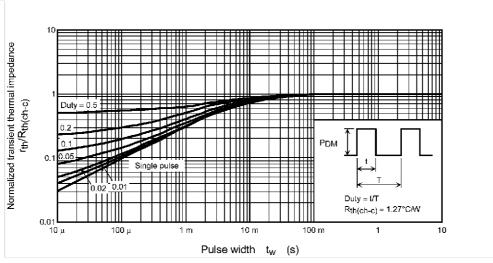


Fig. 8.12 r_{th}/R_{th(ch-c)} - t_w (Guaranteed Maximum)

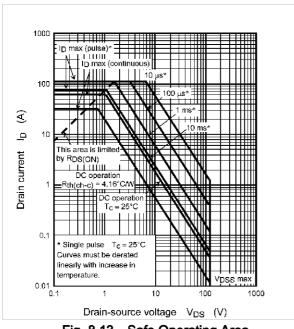


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

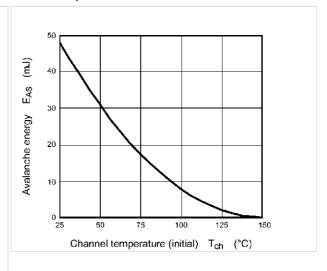


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

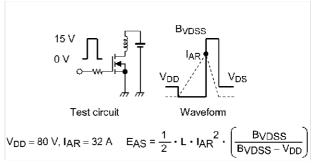


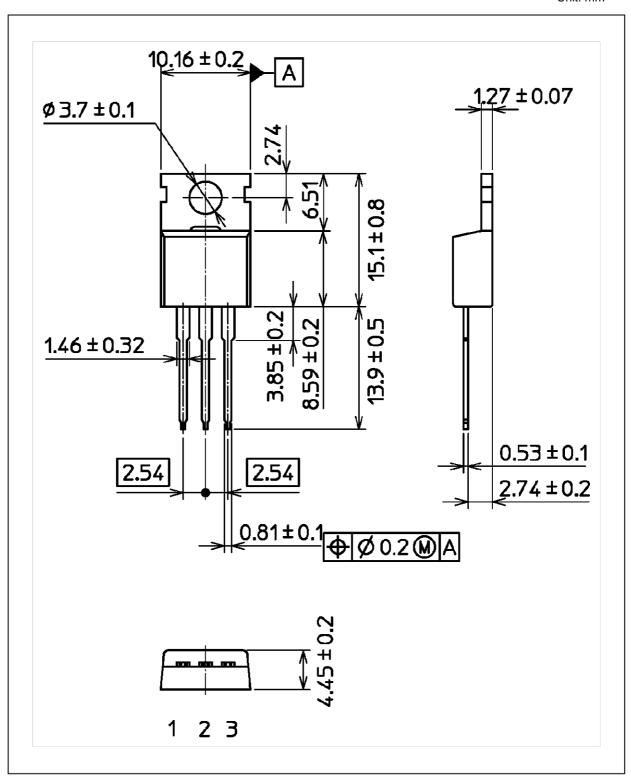
Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	



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